

A94 TRANSISTOR (PNP)

FEATURES

Power dissipation

$$P_{CM}: 0.625 \text{ W (Tamb=25}^\circ\text{C)}$$

Collector current

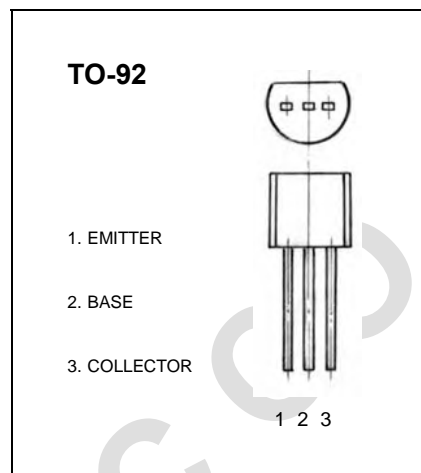
$$I_{CM}: -0.2 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO}: -400 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^\circ\text{C to } +150^\circ\text{C}$$



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}, I_E = 0$	-400			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1 \text{ mA}, I_B = 0$	-400			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu\text{A}, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -400\text{V}, I_E = 0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -400\text{V}, I_B = 0$			-5	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4\text{V}, I_C = 0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -10\text{V}, I_C = -10 \text{ mA}$	80		300	
	$h_{FE(2)}$	$V_{CE} = -10\text{V}, I_C = -1\text{mA}$	70			
	$h_{FE(3)}$	$V_{CE} = -10\text{V}, I_C = -100 \text{ mA}$	60			
Collector-emitter saturation voltage	$V_{CE}(\text{sat})$	$I_C = -10 \text{ mA}, I_B = -1\text{mA}$			-0.2	V
	$V_{CE}(\text{sat})$	$I_C = -50 \text{ mA}, I_B = -5\text{mA}$			-0.3	V
Base-emitter saturation voltage	$V_{BE}(\text{sat})$	$I_C = -10 \text{ mA}, I_B = -1 \text{ mA}$			-0.75	V
Transition frequency	f_T	$V_{CE} = -20\text{V}, I_C = -10\text{mA}$ $f = 30\text{MHz}$	50			MHz